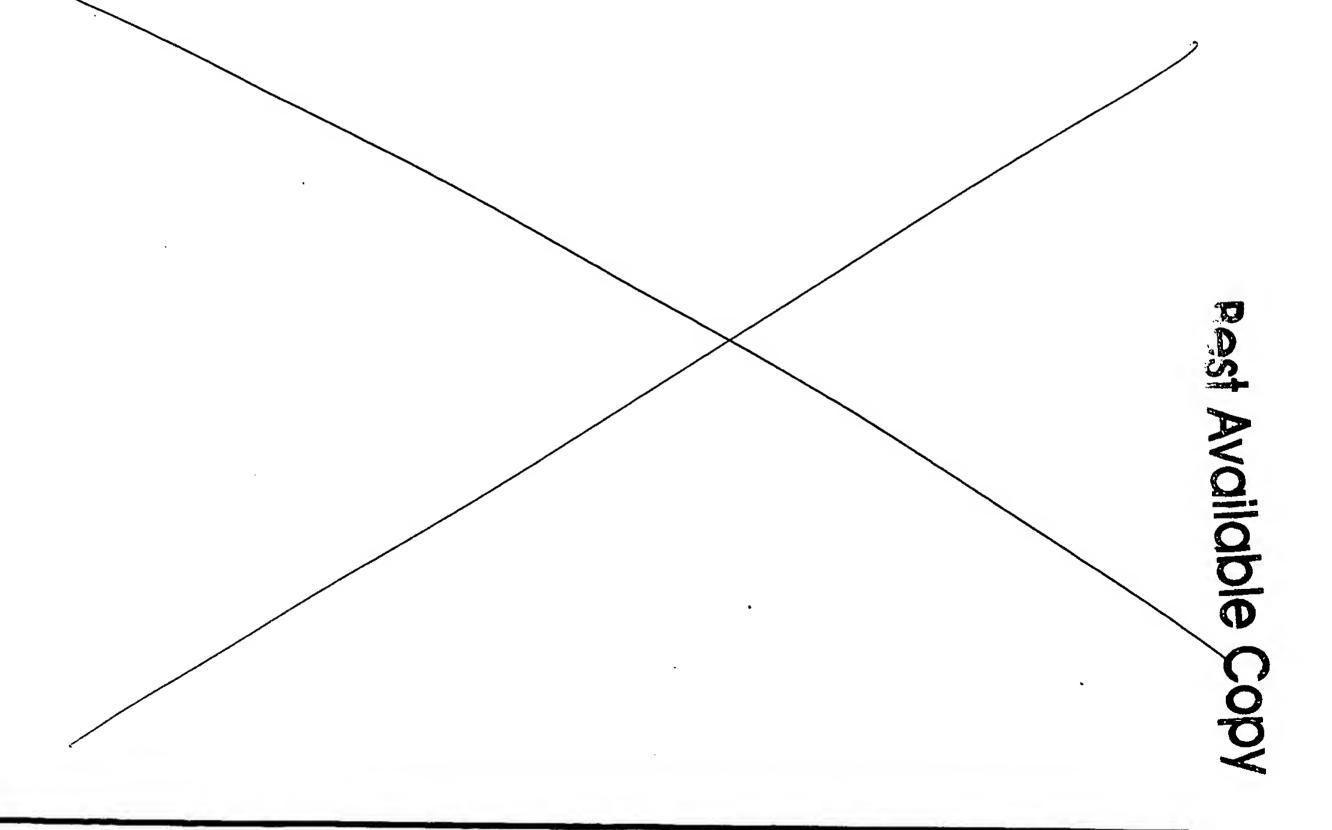
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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid CMS control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** 10/634,274 STATEMENT BY APPLICANT Use as many sheets a hecessary **Filing Date** August 5, 2003 **First Named Inventor** Farrar, Paul 2823 **Group Art Unit Examiner Name** Kebede, Brook & TRADENADY Attorney Docket No: 1303.110US1 Sheet 1 of 1

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Examiner Initials*	Cite No ¹	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the Item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published.	1.		



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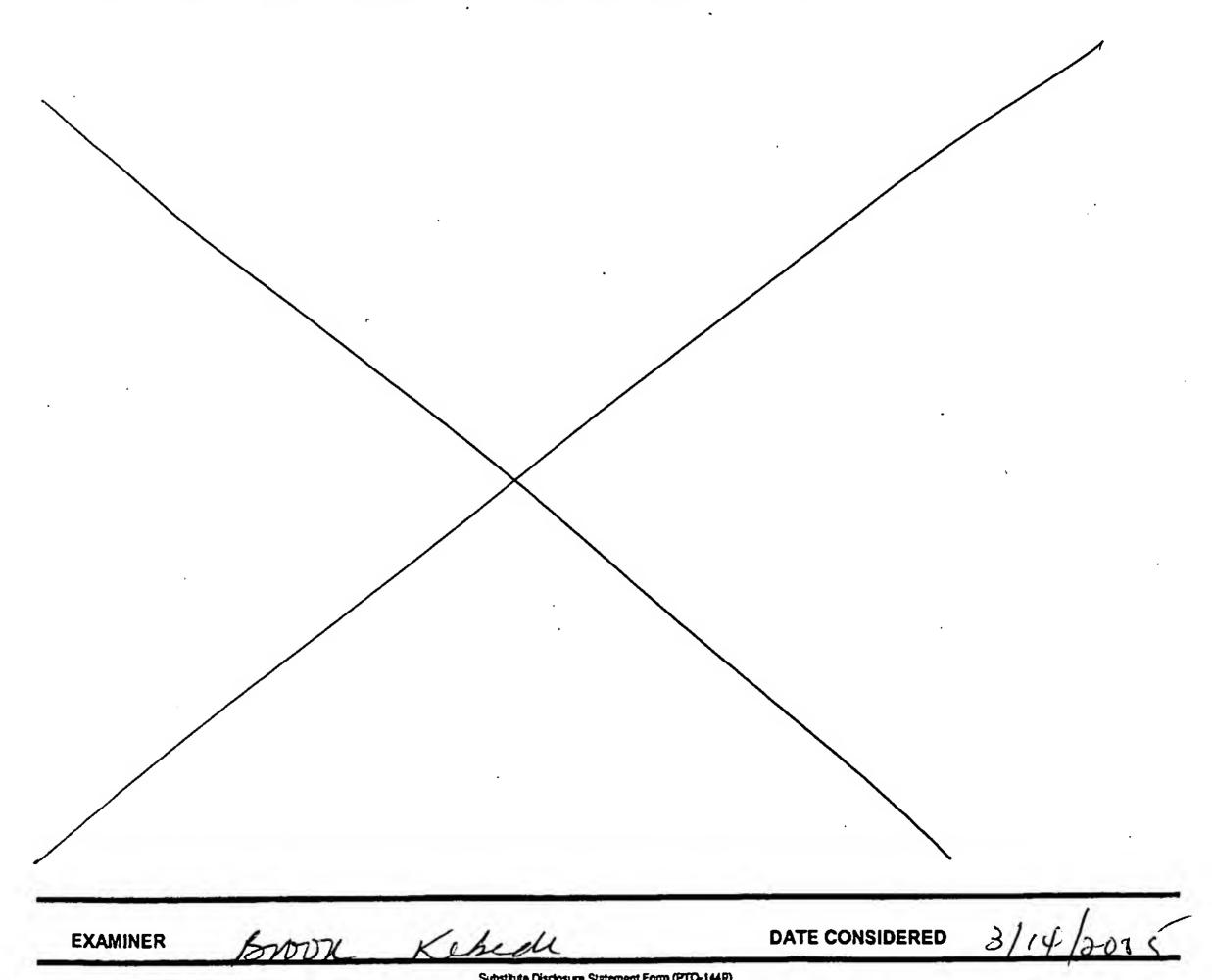
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INFORMATION DISCLOSURE	Application Number	10/634,274
STATEMENT BY APPLICANT (Use as many sheets as necessary)	Filing Date	August 5, 2003
Ose as many shoots as necessary	First Named Inventor	Farrar, Paul
SEP 10 2004 2	Group Art Unit	2823
	Examiner Name	Kebede, Brook
Sheet 1 of 1	Attorney Docket No: 1	303.110US1

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l	First Named Inventor	Farrar, Paul
	Group Art Unit	2818 2823
	Examiner Name	Unknown- B. KEBEDE

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For	2002/0028552	03/07/2002	Lee, Ki-Young, et al.	438	243	09/03/1999
Pork	2002/0096768	07/25/2002	Joshi, Rajiv V.	257	750	01/18/2002
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Bu	US-4,386,116	05/31/1983	Nair, Krishna K., et al.	427	99	12/24/1981
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BU	US-4,423,547	01/03/1984	Farrar, P. A., et al.	29	571	06/01/1981
Bu	US-4,565,157	01/21/1986	Brors, D. L., et al.	118	719	03/29/1983
BK	US-4,574,095	03/04/1986	Baum, Thomas H., et al.	427	53.1	11/19/1984
Bre	US-4,762,728	08/09/1988	Keyser, T., et al.	427	38	11/26/1985
BN	US-4,788,082	11/29/1988	Schmitt, Jerome J.	427	248.1	12/12/1985
Bu	US-4,847,111	07/11/1989	Chow, Yu C., et al.	427	38	06/30/1988
Bu	US-4,931,410	06/05/1990	Tokunaga, Takafumi, et al.	437	189	08/25/1988
BU	US-4,948,459	08/14/1990	Van Laarhoven, et al.	156	643	01/04/1989
ON	US-4,962,058	10/09/1990	Cronin, John E., et al.	437	187	04/14/1989
BIL	US-4,996,584	02/26/1991	Young, P. L., et al.	357	71	10/13/1988
BN	US-5,019,531	05/28/1991	Awaya, N., et al.	437	180	05/19/1989
BU	US-5,034,799	07/23/1991	Tomita, K., et al.	357	71	02/14/1990
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Bul	US-5,100,499	03/31/1992	Douglas, M. A.	156	635	06/25/1991
BR	US-5,130,274	07/14/1992	Harper, J. M., et al.	437	195	04/05/1991
BU	US-5,149,615	09/22/1992	Chakravorty, K. K., et al.	430	313 .	01/08/1991
BU	US-5,158,986	10/27/1992	Cha, S. W., et al.	521	82	04/05/1991
BN	US-5,173,442	12/22/1992	Carey, D. H.	437	173	03/24/1992
BIL	US-5,231,056	07/27/1993	Sandhu, G. S.	437	200	01/15/1992
BIL	US-5,240,878	08/31/1993	Fitzsimmons, J., et al.	437	187	04/26/1991
BU	US-5,243,222	09/07/1993	Harper, J. M., et al.	257	774	01/08/1992
BN	US-5,256,205	10/26/1993	Schmitt III, Jerome J., et al.	118	723	01/07/1992
BIL	US-5,334,356	08/02/1994	Baldwin, D. F., et al.	422	133	08/24/1992
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Substitute for form 1449A/PTO	Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/634274	
	Filing Date	August 5, 2003	
	First Named Inventor	Farrar, Paul	
	Group Art Unit	2818 2823	
	Examiner Name	Unknown B. KEBEDE	
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BN	US-5,384,284	01/24/1995	Doan, T.T., et al.	437	190	10/01/1993
RU	US-5,413,687	05/09/1995	Barton, C. L., et al.	204	192.14	11/27/1991
131	US-5,426,330	06/20/1995	Joshi, R. V., et al.	257	752	09/21/1993
BN	US-5,442,237	08/15/1995	Hughes, Henry G., et al.	257	759	02/04/1994
BK	US-5,447,887	09/05/1995	Filipiak, Stanley, et al.	437	200	04/01/1994
1321	US-5,461,243	10/24/1995	Ek, Bruce A., et al.	257	190	10/29/1993
BU	US-5,470,789	11/28/1995	Misawa, N.	437	190	03/07/1995
BN	US-5,470,801	11/28/1995	Kapoor, Ashok K., et al.	437	238	06/28/1993
BU	US-5,476,817	12/19/1995	Numata, K.	437	195	05/31/1994
BN	US-5,495,667	03/05/1996	Farnworth, Warren M., et al.	29	843	11/07/1994
BN	US-5,506,449	04/09/1996	Nakano, Tadashi, et al.	257	758	03/23/1994
BR	US-5,529,956	06/25/1996	Morishita, Y.	437	195	09/28/1994
BIL	US-5,538,922	07/23/1996	Cooper, K J., et al.	437	195	01/25/1995
BN	US-5,539,060	07/23/1996	Tsunogae, Y., et al.	525	338	10/13/1995
RI	US-5,595,937	01/21/1997	Mikagi, K.	437	192	04/12/1996
BU	US-5,609,721	03/11/1997	Tsukune, A, et al.	156	646.1	01/03/1995
Bu	US-5,625,232	04/29/1997	Numata, K., et al.	257	758	07/15/1994
BR	US-5,635,253	06/03/1997	Canaperi, Donald F., et al.	427	437	06/07/1995
BIL	US-5,654,245	08/05/1997	Allen, Gregory L.	438	629	03/23/1993
BIL	US-5,662,788	09/02/1997	Sandhu, G., et al.	205	87	06/03/1996
BIL	US-5,670,420	09/23/1997	Choi, Kyeong K.	437	189	11/08/1995
1811	US-5,674,787	10/07/1997	Zhao, Bin, et al.	437	230	01/16/1996
BK	US-5,675,187	10/07/1997	Numata, K., et al.	257	758	05/16/1996
BN	US-5,679,608	10/21/1997	Cheung, Robin W., et al.	437	195	06/05/1995
BIL	US-5,681,441	10/28/1997	Svendsen, Leo G., et al.	205	114	12/22/1992
BN	US-5,695,810	12/09/1997	Dubin, Valery M., et al.	427	96	11/20/1996
Bu	US-5,719,089	02/17/1998	Cherng, Meng-Jaw, et al.	438	637	06/21/1996
BN	US-5,719,410	02/17/1998	Suehiro, Shintaro, et al.	257	77	12/16/1996
BIL	US-5,739,579	04/14/1998	Chiang, Chien, et al.	257	635	09/10/1996
BN	US-5,763,953	06/09/1998	Iljima, T., et al.	257	762	01/18/1996
	US-5,780,358	07/14/1998	Zhou, M. S.	438	645	04/08/1996
1810	US-5,785,570	07/28/1998	Bruni, M. D.	445	52	07/25/1995

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Substitute for form 1449A/PTO	Complete if Known	required to respond to a collection of distribution threats it contains a valid CMU control numb		
STATEMENT BY APPLICANT Use as many sheets as necessary)	Application Number	10/634274		
	Filing Date	August 5, 2003		
	First Named Inventor	Farrar, Paul		
	Group Art Unit	2818 2823		
	Examiner Name	Unknown B. KEBEDE		
Sheet 3 of 12	Attorney Docket No: 1303.110US1			

Box	US-5,792,522	08/11/1998	Jin, S., et al.	427	575	09/18/1996
Box	US-5,801,098	09/01/1998	Fiordalice, R., et al.	438	653	09/03/1996
BIL	US-5,814,557	09/29/1998	Venkatraman, Ramnath, et al.	438	622	05/20/1996
BX	US-5,821,168	10/13/1998	Jain, Ajay	438	692	07/16/1997
BIL	US-5,824,599	10/20/1998	Schacham-Diamond, Yosef, et al.	438	678	01/16/1996
por	US-5,858,877	01/12/1999	Dennison, C. H., et al.	438	700	01/21/1997
BU	US-5,891,797	04/06/1999	Farrar, P. A.	438	619	10/20/1997
BU	US-5,891,804	04/06/1999	Havemann, R. H., et al.	438	674	04/14/1997
BU	US-5,893,752	04/13/1999	Zhang, J., et al.	438	687	12/22/1997
BU	US-5,895,740	04/20/1999	Chien, Rong-Wu, et al.	430	313	11/13/1996
Bu	US-5,897,370	04/27/1999	Joshi, R. V., et al.	438	632	10/28/1996
BNL	US-5,907,772	05/25/1999	Iwasaki, Haruo	438	253	02/26/1997
BU	US-5,911,113	06/08/1999	Yao, G., et al.	438	649	03/18/1997
BN	US-5,913,147	06/15/1999	Dubin, Valery, et al.	438	687	01/21/1997
BIL	US-5,925,930	07/20/1999	Farnworth, Warren M., et al.	257	737	05/21/1996
Bu	US-5,930,669	07/27/1999	Uzoh, Cyprian	438	627	04/03/1997
BU	US-5,932,928	08/03/1999	Clampitt, D. A.	257	758	07/03/1997
BIL	US-5,933,758	08/03/1999	Jain, A.	438	687	05/12/1997
BU	US-5,940,733	08/17/1999	Beinglass, Israel, et al.	438	655	07/29/1997
Bu	US-5,948,467	09/07/1999	Nguyen, T., et al.	427	99	07/24/1998
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BN	US-5,968,333	10/19/1999	Nogami, T., et al.	205	184	04/07/1998
BU	US-5,969,422	10/19/1999	Ting, C., et al.	257	762	05/15/1997
BIL	US-5,972,179	10/26/1999	Chittipeddi, , et al.	204	192.17	09/30/1997
Bu	US-5,972,804	10/26/1999	Tobin, Philip J., et al.	438	786	11/03/1997
Bol	US-5,976,710	11/02/1999	Sachdev, K. G., et al.	428	620	04/10/1997
BU	US-5,981,350	11/09/1999	Geusic, Joseph E., et al.	438	386	05/29/1998
BN	US-5,985,759	11/16/1999	Kim, E., et al.	438	653	02/24/1998
BU	US-5,989,623	11/23/1999	Chen, Liang-Yuh, et al.	427	97	08/19/1997
BU	US-5,994,777	11/30/1999	Farrar, P. A.	257	758	08/26/1998
BU	US-6,001,730	12/14/1999	Farkas, J., et al.	438	627	10/20/1997
BU	US-6,008,117	12/28/1999	Hong, Qi-Zhong, et al.	438	629	03/19/1997
BU	US-6,015,465	01/18/2000	Kholodenko, A., et al.	118	719	04/08/1998
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/634274		
	Filing Date	August 5, 2003		
	First Named Inventor	Farrar, Paul		
	Group Art Unit	2818 2823		
	Examiner Name	Unknown B. KEBEDE		
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(Use as many sheets as necessary)	Filing Date	August 5, 2003
•	First Named Inventor	Farrar, Paul
	Group Art Unit	2818 2823
	Examiner Name	Unknown B. KEBEDE
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	Group Art Unit			
	Examiner Name	Unknown BIKEBEDE		
Sheet 6 of 12	Attorney Docket No: 1	1303.110US1		

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(Use as many sheets as necessary)	Filing Date	August 5, 2003		
	First Named Inventor	Farrar, Paul 2818		
	Group Art Unit			
	Examiner Name	Unknown		
Sheet 7 of 12	Attorney Docket No: 1303.110US1			

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Attorney Docket No: 1303.110US1		
Examiner Name	Unknown B. KEBEDE	
Group Art Unit	2818 2823	
First Named Inventor	August 5, 2003 Farrar, Paul	
Filing Date		
Application Number	10/634274	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/634274
(Use as many sheets as necessary)	Filing Date	August 5, 2003
	First Named Inventor	Farrar, Paul
	Group Art Unit	2818
	Examiner Name	Unknown
Sheet 11 of 12	Attorney Docket No: 1	1303.110US1

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Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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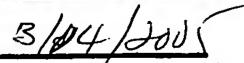
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	Group Art Unit	2818-2823
	Examiner Name	Unknown B. KEBEDE
Sheet 12 of 12	Attorney Docket No: 1303.110US1	

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